

ABSTRACT**METHOD OF FABRICATION OF A SEMICONDUCTOR ELEMENT COMPRISING
A HIGHLY RESISTIVE SUBSTRATE**

The invention concerns a method of fabrication of a semiconductor element, the method involving a step of rapid heat treatment exposing a substrate comprising a base having a resistivity greater than 1000 Ohm.cm to a peak temperature able to deteriorate the resistivity of the base. According to the invention, the step of rapid heat treatment is followed by a curing heat treatment exposing the substrate to a curing temperature between 800°C and 1250°C and having a cooldown rate less than 5°C/sec when the curing temperature is between 1250°C and 1150°C, less than 20°/sec when the curing temperature is between 1150°C and 1100°C, and less than 50°C/sec when the curing temperature is between 1100°C and 800°C.

Figure 6